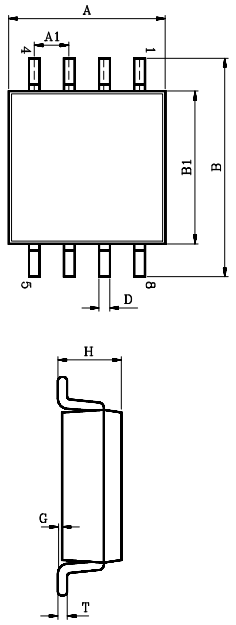
KIC7W126FU

SILICON MONOLITHIC CMOS
DIGITAL INTEGRATED CIRCUIT

DUAL BUS BUFFER

The KIC7W126FU is a high speed C^2MOS DUAL BUS BUFFERS fabricated with silicon gate C^2MOS technology. It achieve the high speed operation similar to equivalent LSTTL while maintaining the C^2MOS low power dissipation. The require 3-state control input G to be set low to place the output into the high impedance.
All inputs are equipped with protection circuits against static discharge or transient excess voltage.



DIM	MILLIMETERS
A	2.9±0.1
A1	0.65
B	4.0±0.1
B1	2.8±0.1
D	0.2+0.1/−0.05
G	0−0.1
H	1.1±0.1
T	0.15±0.05

SM8

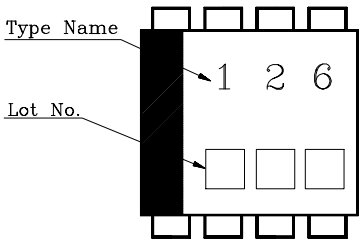
FEATURES

- High Speed : t_{pd}=10ns(Typ.) at V_{CC}=5V.
- Low Power Dissipation : I_{CC}=2μA(Max.) at Ta=25℃.
- High Noise Immunity : V_{NIH}=V_{NIL}=28% V_{CC}(Min.).
- Output Drive Capability : 15 LSTTL Loads.
- Symmetrical Output Impedance : $|I_{OH}|$=I_{OL}=6mA(Min.)
- Balanced Propagation Delays : $t_{pLH} \fallingdotseq t_{pHL}$
- Wide Operating Voltage Range : $V_{CC(opr)}$=2~6V.

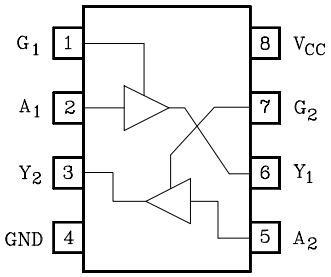
MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~V_{CC}+0.5	V
DC Output Voltage	V_{OUT}	-0.5~V_{CC}+0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±20	mA
DC Output Current	I_{OUT}	±35	mA
DC V_{CC}/Ground Current	I_{CC}	±37.5	mA
Power Dissipation	P_D	300	mW
Storage Temperature	T_{stg}	-65~150	℃
Lead Temperature (10s)	T_L	260	℃

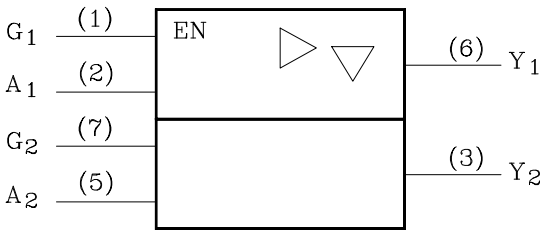
MARKING



PIN CONNECTION(TOP VIEW)



LOGIC DIAGRAM



TRUTH TABLE

INPUTS		OUTPUTS
G	A	Y
L	X	Z
H	L	L
H	H	H

X : Don't Care
Z : High Impedance

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~V_{CC}	V
Output Voltage	V_{OUT}	0~V_{CC}	V
Operating Temperature	T_{opr}	-40~85	℃
Input Rise and Fall Time	t_r, t_f	0~1000 (V_{CC}=2.0V) 0~ 500 (V_{CC}=4.5V) 0~ 400 (V_{CC}=6.0V)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CIR-CUIT	TEST CONDITION			Ta=25℃			Ta=-40~85℃		UNIT
					V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	V_{IH}	-	-		2.0 4.5 6.0	1.5 3.15 4.2	- - -	- - -	1.5 3.15 4.2	- - -	V
Low-Level Input Voltage	V_{IL}	-	-		2.0 4.5 6.0	- - -	- - -	0.5 1.35 1.8	- - -	0.5 1.35 1.8	V
High-Level Output Voltage	V_{OH}	-	V_{IN}=V_{IH}	I_{OH}=-20μA	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	- - -	1.9 4.4 5.9	- - -	V
				I_{OH}=-6mA I_{OH}=-7.8mA	4.5 6.0	4.18 5.68	4.31 5.80	- -	4.13 5.63	- -	
Low-Level Output Voltage	V_{OL}	-	V_{IN}=V_{IH} or V_{IL}	I_{OL}=20μA	2.0 4.5 6.0	- - -	0.0 0.0 0.0	0.1 0.1 0.1	- - -	0.1 0.1 0.1	V
				I_{OL}=6mA I_{OL}=7.8mA	4.5 6.0	- -	0.17 0.18	0.26 0.26	- -	0.33 0.33	
3-State Output Off-State Current	I_{OZ}	-	V_{IN}=V_{IH} or V_{IL} V_{OUT}=V_{CC} or GND		6.0	-	-	±0.5	-	±5.0	μA
Input Leakage Current	I_{IN}	-	V_{IN}=V_{CC} or GND		6.0	-	-	±0.1	-	±1.0	
Quiescent Supply Current	I_{CC}	-	V_{IN}=V_{CC} or GND		6.0	-	-	2.0	-	20.0	

AC ELECTRICAL CHARACTERISTICS (Input $t_r=t_f=6ns$)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION			Ta=25℃			Ta=-40~85℃		UNIT
				C_L	V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	-	-	50	2.0 4.5 6.0	- - -	20 6 5	60 12 10	- - -	75 15 13	ns
Propagation Delay Time	t_{pLH} t_{pHL}	-	-	50	2.0 4.5 6.0	- - -	30 11 10	90 18 15	- - -	115 23 20	
				150	2.0 4.5 6.0	- - -	42 14 12	130 26 22	- - -	165 33 28	
Output Enable Time	t_{pZL} t_{pZH}	-	R_L=1kΩ	50	2.0 4.5 6.0	- - -	30 11 10	90 18 15	- - -	115 23 20	
				150	2.0 4.5 6.0	- - -	42 14 12	130 26 22	- - -	165 33 28	
Output Disable Time	t_{pLZ} t_{pHZ}	-	R_L=1kΩ	50	2.0 4.5 6.0	- - -	24 12 10	100 20 17	- - -	125 25 21	
Input Capacitance	C_{IN}	-	-	-	-	-	5	10	-	10	pF
Output Capacitance	C_{OUT}	-	-	-	-	-	10	-	-	-	
Power Dissipation Capacitance	C_{PD}	-	(Note 1)	-	-	-	32	-	-	-	

Note 1 : C_{PD} is defined as the value of internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation
: $I_{CC(opr)}=C_{PD}\cdot V_{CC}\cdot f_{IN}+I_{CC}/2$ (per gate)